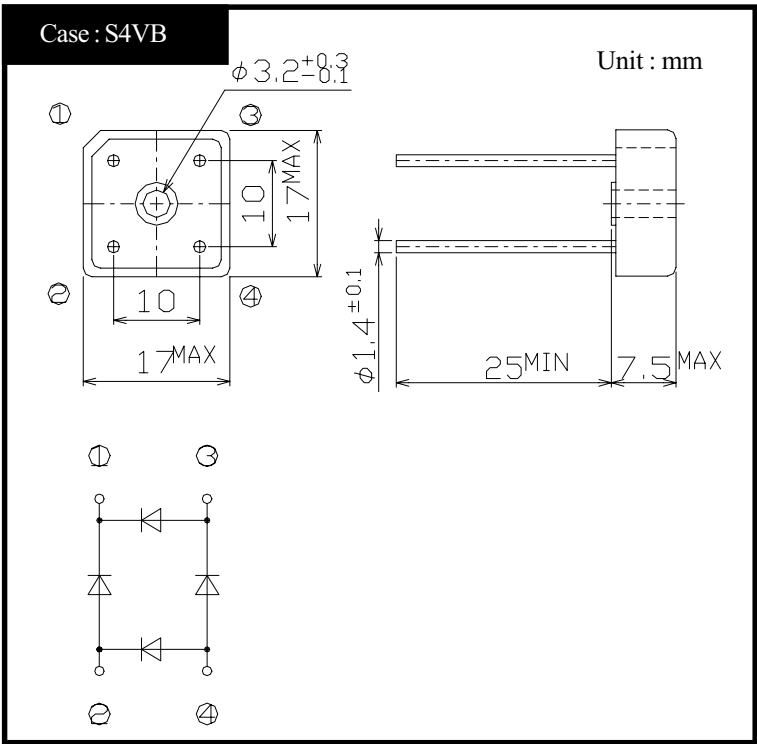


S4VB20

200V 4A

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings

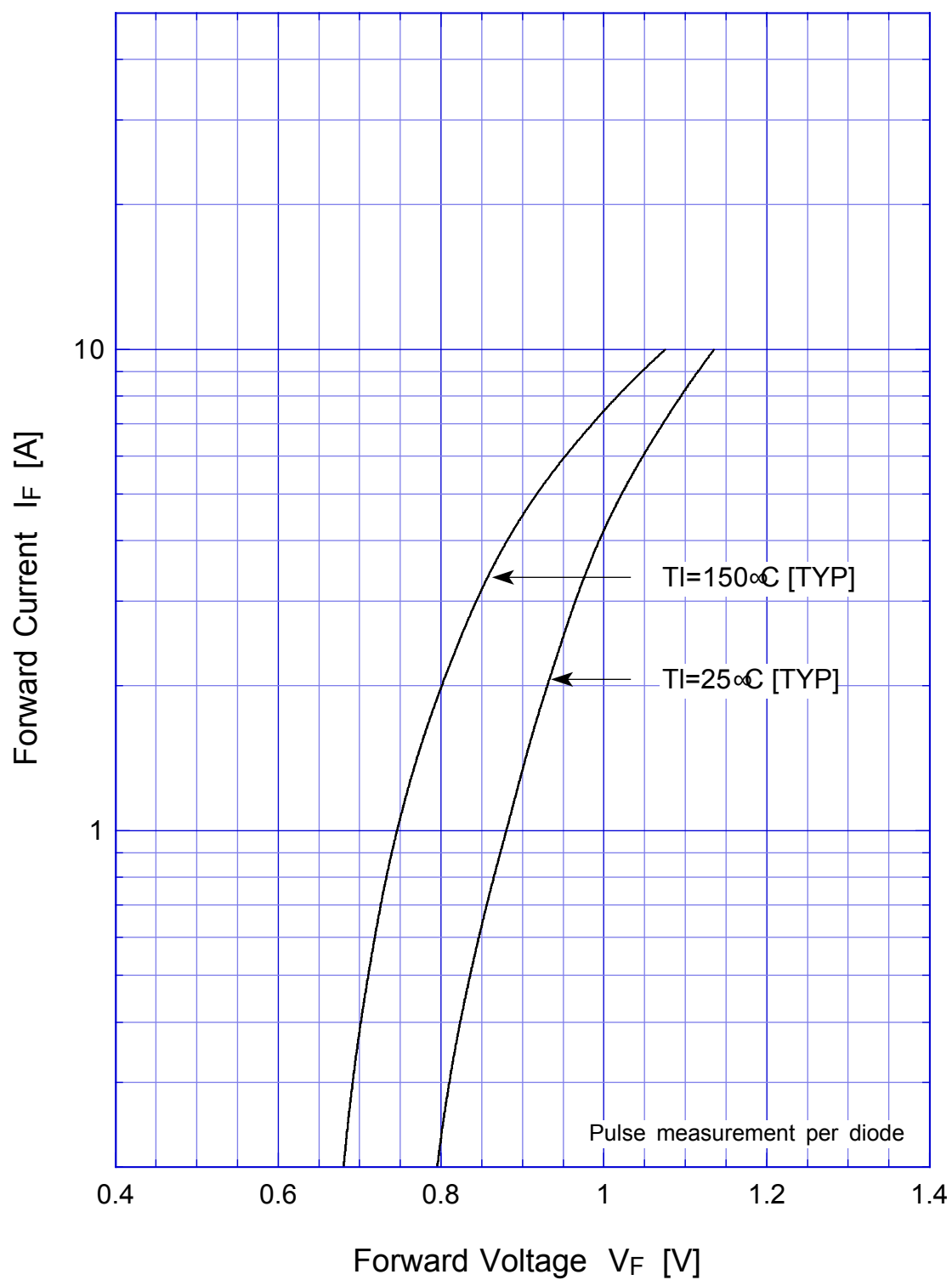
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-40~150	°C
Operating Junction Temperature	T _j		150	°C
Maximum Reverse Voltage	V _{RM}		200	V
Average Rectified Forward Current	I _O	50Hz sine wave, R-load, T _a =40°C With heatsink θ _{fa} =10°C/W	4	A
		50Hz sine wave, R-load, T _a =40°C Without heatsink	2.6	
Peak Surge Forward Current	I _{FSM}	50Hz sine wave, Non-repetitive 1cycle peak value, T _j =25°C	80	A
Current Squared Time	I ² t	1ms≤t<10ms T _j =25°C	32	A ² s
Mounting Torque	TOR	(Recommended torque : 0.5N·m)	0.8	N·m

● Electrical Characteristics (T_i=25°C)

Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	V _F	I _F =2A, Pulse measurement, Rating of per diode	Max.1.05	V
Reverse Current	I _R	V _R =V _{RM} , Pulse measurement, Rating of per diode	Max.10	μA
Thermal Resistance	θ _{jl}	junction to lead	Max.4.5	°C/W

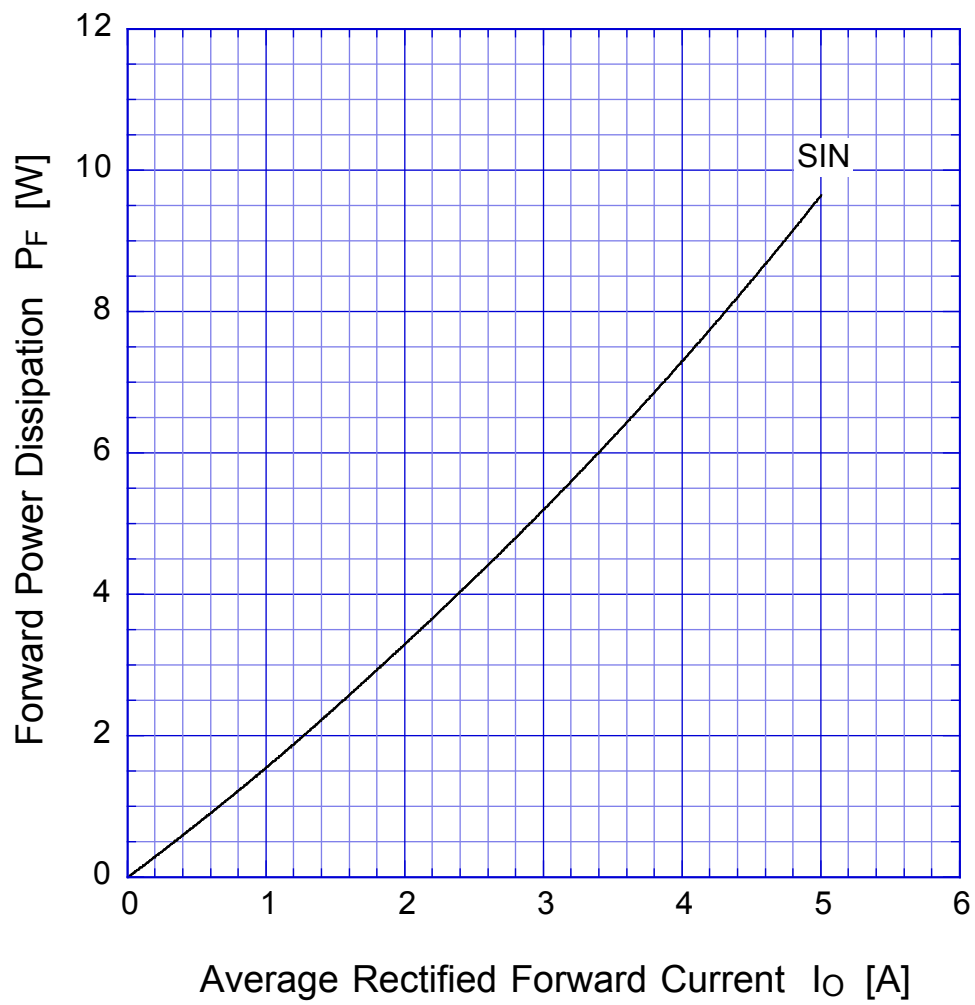
S4VBx

Forward Voltage



S4VBx

Forward Power Dissipation

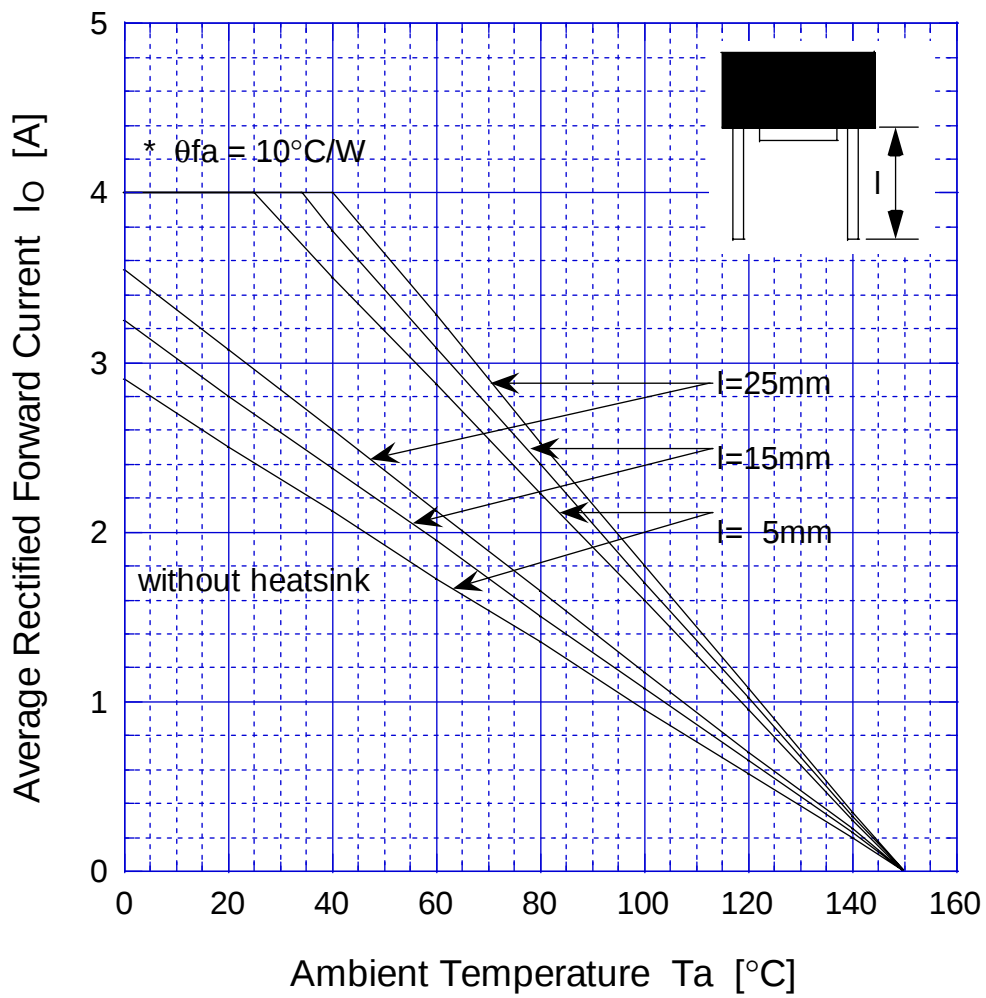


$T_j = 150^{\circ}\text{C}$

Sine wave

S4VBx

Derating Curve



Sine wave

R-load

Free in air

* with thermal compound, TOR=0.3N-m

S4VBx

Peak Surge Forward Capability

